



US009972668B2

(12) **United States Patent**
Shi et al.

(10) **Patent No.:** **US 9,972,668 B2**
(45) **Date of Patent:** **May 15, 2018**

(54) **OLED DISPLAY DEVICE AND
MANUFACTURE METHOD THEREOF**

(2013.01); *H01L 27/3262* (2013.01); *H01L*
2227/323 (2013.01); *H01L 2251/301*
(2013.01); *H01L 2251/308* (2013.01); *H01L*
2251/558 (2013.01)

(71) Applicant: **Shenzhen China Star Optoelectronics
Technology Co., Ltd.**, Shenzhen,
Guangdong (CN)

(58) **Field of Classification Search**
CPC combination set(s) only.
See application file for complete search history.

(72) Inventors: **Longqiang Shi**, Guangdong (CN);
Yifan Wang, Guangdong (CN)

(56) **References Cited**

(73) Assignee: **Shenzhen China Star Optoelectronics
Technology Co., Ltd.**, Shenzhen,
Guangdong (CN)

U.S. PATENT DOCUMENTS

(*) Notice: Subject to any disclaimer, the term of this
patent is extended or adjusted under 35
U.S.C. 154(b) by 0 days. days.

2003/0160247 A1* 8/2003 Miyazawa *H01L 51/5262*
257/79
2003/0201445 A1* 10/2003 Park *H01L 27/3253*
257/79

* cited by examiner

(21) Appl. No.: **15/821,844**

Primary Examiner — Ratisha Mehta

(22) Filed: **Nov. 24, 2017**

(74) *Attorney, Agent, or Firm* — Andrew C. Cheng

(65) **Prior Publication Data**

US 2018/0108719 A1 Apr. 19, 2018

(57) **ABSTRACT**

Related U.S. Application Data

(62) Division of application No. 14/424,965, filed on Feb.
27, 2015.

A method for manufacturing an OLED display device that includes pixel areas is provided. A first and a second substrates are provided. TFTs are arranged on the first substrate. A passivation layer is formed on the TFTs such that the passivation layer includes a concave area formed in a surface thereof to expose a part of a drain of each of the TFTs. A transparent anode is formed on the second substrate. Partition walls are arranged on the transparent anode to defined therebetween transmission holes respectively corresponding to the pixel areas. An organic layer is formed on the transparent anode and located in the transmission holes. A metal cathode is formed on the organic layer and the partition walls such that the metal cathode is receivable into the concave area and electrically engageable with the exposed part of the drain of each of the TFTs.

(51) **Int. Cl.**

H01L 27/32 (2006.01)

H01L 51/00 (2006.01)

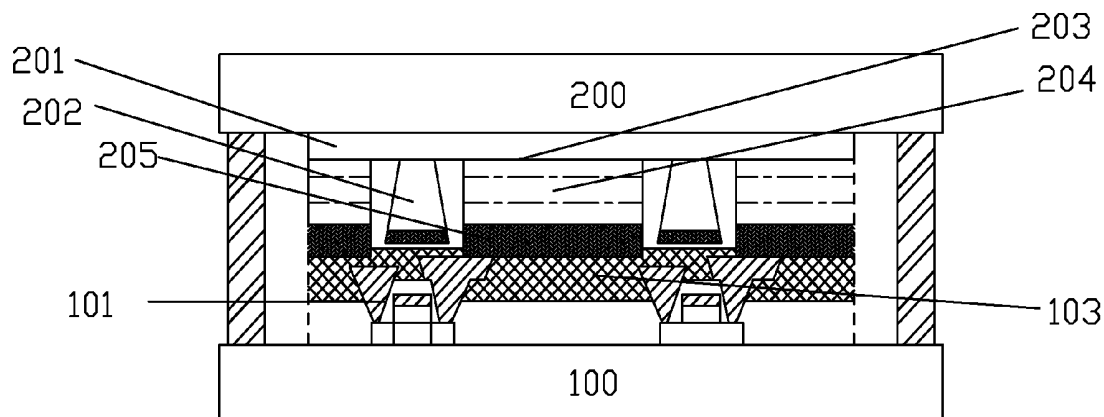
H01L 51/52 (2006.01)

H01L 51/56 (2006.01)

(52) **U.S. Cl.**

CPC *H01L 27/3253* (2013.01); *H01L 27/3246*
(2013.01); *H01L 27/3248* (2013.01); *H01L*
51/0024 (2013.01); *H01L 51/5206* (2013.01);
H01L 51/5221 (2013.01); *H01L 51/56*

5 Claims, 4 Drawing Sheets



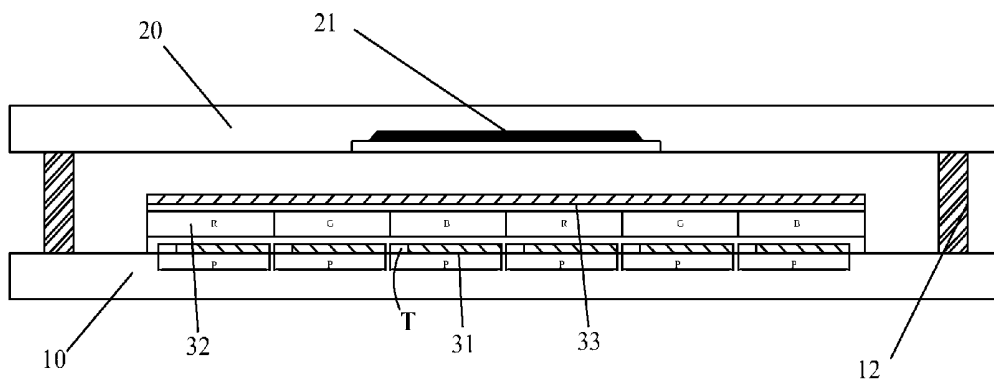


Fig. 1

(Prior Art)

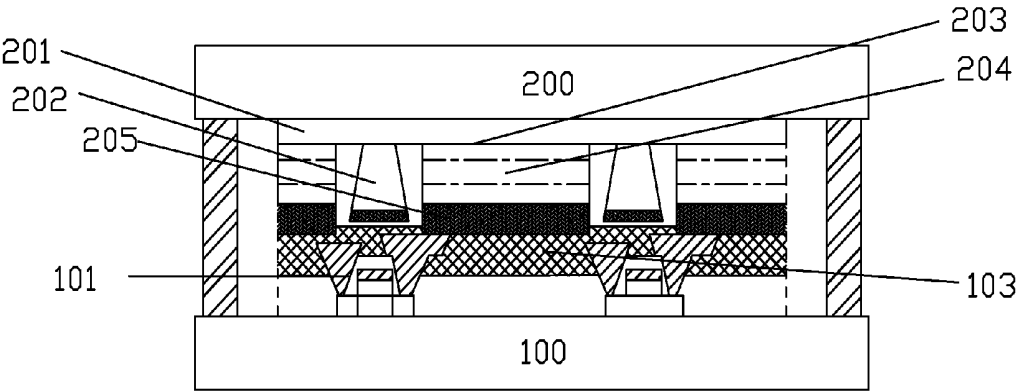


Fig. 2

step 1, forming a thin film transistor (101), comprising a gate (101a), a source metal layer (101b), a drain metal layer (101c) on a first substrate, wherein a thickness of the source metal layer (101b) is smaller than a thickness of the drain metal layer (101c);

step 2, forming a passivation layer (103) on the source metal layer (101b), the drain metal layer (101c) and the first substrate (100), and a concave area (101d) of the passivation layer (103) and a convex area (101e) adjacent to the concave area (101d) is formed by a formation process; wherein a bottom of the concave area (101d) is aligned with a top surface of the drain metal layer (101c) and higher than a top surface of the source metal layer (101b) to expose a part of the drain metal layer (101c);

step 3, forming a transparent anode (201) on a second substrate (200);

step 4, forming partition walls (202) on the transparent anode (201), and the partition walls (202) comprise a plurality of transmission holes (203) corresponding to all pixel areas;

step 5, forming an organic layer (204) in the transmission holes (203) on the transparent anode (201);

step 6, forming a metal cathode (205) on the organic layer (204) and the partition walls (202);

step 7, laminating the first substrate (100) and the second substrate (200), and the metal anode (205) on the organic layer (204) correspondingly joints into the concave area (101d) and fits the bottom of the concave area (101d), and the metal cathode (205) is connected to the drain metal layer (101c) via the concave area (101d).

Fig. 3

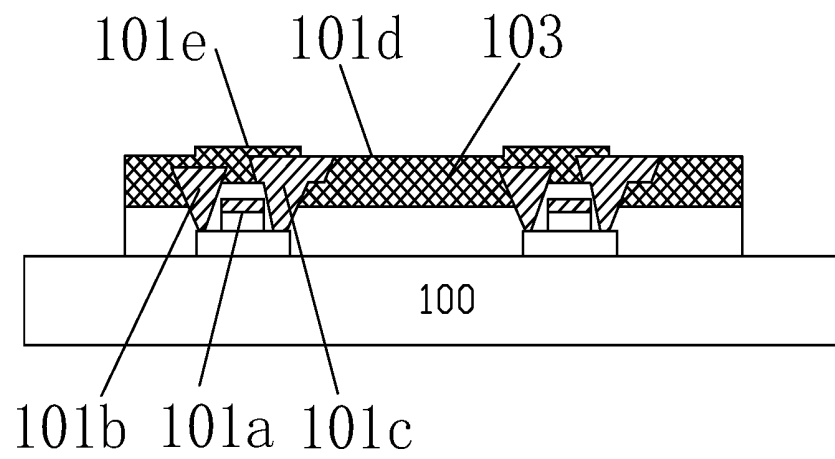


Fig. 4

OLED DISPLAY DEVICE AND MANUFACTURE METHOD THEREOF

CROSS REFERENCE TO RELATED APPLICATIONS

This is a divisional application of co-pending patent application Ser. No. 14/424,965, filed on Feb. 27, 2015, which is a national stage of PCT Application Number PCT/CN2015/072506, filed on Feb. 9, 2015, claiming foreign priority of Chinese Patent Application Number 201410742800.0, filed on Dec. 8, 2014.

FIELD OF THE INVENTION

The present invention relates to the field of display technology, and more particularly to an organic light emitting diode (OLED) display device and a manufacture method thereof.

BACKGROUND OF THE INVENTION

Organic light emitting diode (OLED) is a flat panel display technology, which has great prospects for development. It possesses not only extremely excellent display performance but also properties of self-illumination, simple structure, being ultra thin, fast response speed, wide view angle, low power consumption and capability of realizing flexible displaying, and is therefore considered as a "dream display". It has been favored by all large display makers and has become the main selection of the third generation displays.

The OLED display generally comprises a substrate, an anode located on the substrate, an organic emitting layer located on the anode, an electron transport layer located on the organic emitting layer, and a cathode located on the electron transport layer. During operation, holes from the anode and electrons from the cathode are injected into the organic emitting layer. The electrons and holes are combined to generate excited electron-hole pairs, and the excited electron-hole pairs are converted from an excited state to a ground state for achieving illumination.

The OLED can be categorized as passive matrix OLED (PMOLED) and active matrix OLED (AMOLED) according to driving type. The power consumption of the PMOLED is high, and thus, it hinders the application in large-scale display devices. Besides, in PMOLED, the aperture ratio is decreased along with the amount of wirings increased. Therefore, the PMOLED is generally applied for the small-scale display devices. The lighting efficiency of the AMOLED is high, and therefore, it is generally utilized for the large-scale display devices of high resolution.

On the other hand, the AMOLEDs can be categorized into bottom emitting AMOLED display devices and top emitting AMOLED display devices according to the emitting direction of the light from the organic emitting layer.

Referring to FIG. 1, a sectional view of a prior art bottom emitting AMOLED display device is provided. As shown in FIG. 1, the AMOLED display device comprises a first substrate 10 and a second substrate 20, which are separated and oppositely face each other. A plurality of thin film transistors T and a plurality of first electrodes 31 are formed on an inner surface of the first substrate 10, wherein each of the first electrodes 31 is connected to one of the thin film transistors T, and an organic layer 32 is formed on the first electrodes 31 and the thin film transistors T, and second electrodes 33 are formed on the organic layer 32. The

organic layer 32 emits three colors of light in each pixel P, including red light R, green light G and blue light B. The AMOLED display device further comprises: a dryer 21 formed on an inner surface of the second substrate 20 to remove moisture and air that possibly invade into a space between the first and second substrates 10, 20. Seal 12 is arranged between the first and second substrates 10, 20 and surrounds the first and second electrodes 31, 33, the organic layer 32, and the thin film transistors T for protecting these elements from external moisture and air.

In the bottom emitting AMOLED display device shown in FIG. 1, the light emitting therefrom passes through the bottom where the thin film transistors are formed, and this lowers the aperture ratio as compared with the top emitting AMOLED display device. On the other hands, the top emitting AMOLED display device possesses a high aperture ratio but the cathode is generally built on the organic layer so that choice of the material for manufacturing the cathode is restricted. Thus, the transmittance is restricted and display effect is degraded.

SUMMARY OF THE INVENTION

An objective of the present invention is to provide an organic light emitting diode (OLED) display device, which provides a top emitting mode that shows high transmittance and provides a high aperture ratio.

Another objective of the present invention is to provide a manufacture method of an OLED display device, which help improve yield and the productivity.

For realizing the aforesaid objectives, the present invention first provides an OLED display device, which comprises: a first substrate, a second substrate spaced from and opposite to the first substrate, a plurality of thin film transistors located on an inner surface of the first substrate, a transparent anode located on an inner surface of the second substrate, a plurality of partition walls located on the transparent anode, transmission holes formed among the partition walls, an organic layer located on the transparent anode and in the transmission holes, and a metal cathode located on the organic layer and the partition walls, wherein the metal cathode is electrically connected to a drain of the thin film transistor.

The thin film transistor comprises a gate, a source metal layer and a drain metal layer, wherein a thickness of the source metal layer is smaller than a thickness of the drain metal layer; a passivation layer is further located on the source metal layer, the drain metal layer and the first substrate, and the passivation layer comprises a concave area and a convex area adjacent to the concave area, and a bottom of the concave area is aligned with a top surface of the drain metal layer and higher than a top surface of the source metal layer to expose a part of the drain metal layer, and the metal anode on the organic layer correspondingly joints into the concave area and fits the bottom of the concave area, and the metal cathode is connected to the drain metal layer via the concave area.

A material of the transparent anode is indium tin oxide.

A material of the metal cathode is one of calcium, aluminum and magnesium.

The organic layer comprises a hole transporting layer contacting the transparent anode, an electron transport layer contacting the metal cathode and an emitting layer located between the hole transporting layer and the electron transport layer.

The present invention further provides a manufacture method of an OLED display device, which comprises the following steps:

Step 1, forming a thin film transistor, which comprises a gate, a source metal layer, a drain metal layer, on a first substrate, wherein a thickness of the source metal layer is smaller than a thickness of the drain metal layer;

Step 2, forming a passivation layer on the source metal layer, the drain metal layer and the first substrate, and applying a formation process to form a concave area and a convex area that is adjacent to the concave area on the passivation layer,

wherein a bottom of the concave area is aligned with a top surface of the drain metal layer and higher than a top surface of the source metal layer to expose a part of the drain metal layer;

Step 3, forming a transparent anode on a second substrate;

Step 4, forming partition walls on the transparent anode, such that the partition walls comprise a plurality of transmission holes respectively corresponding to pixel areas;

Step 5, forming an organic layer in the transmission holes to be located on the transparent anode;

Step 6, forming a metal cathode on the organic layer and the partition walls; and

Step 7, laminating the first substrate and the second substrate, such that the metal cathode on the organic layer corresponds to and joints into the concave area and fits to the bottom of the concave area and the metal cathode is connected to the drain metal layer via the concave area.

As manufacturing respective elements, the concave area of the passivation layer is designed to correspond, in position, to the metal cathode on the organic layer, and an area of the concave area is larger than or equal to an area of the metal cathode on the organic layer, and the metal cathode on the organic layer can be completely jointed in the concave area of the passivation layer when the first substrate and the second substrate are combined together.

In Step 3, a material of the transparent anode is indium tin oxide.

In Step 5, a material of the metal cathode is one of calcium, aluminum and magnesium.

In Step 5, the organic layer comprises a hole transporting layer contacting the transparent anode, an electron transport layer contacting the metal cathode and an emitting layer located between the hole transporting layer and the electron transport layer.

The present invention further provides an OLED display device, which comprises a first substrate, a second substrate spaced from and opposite to the first substrate, a plurality of thin film transistors located on an inner surface of the first substrate, a transparent anode located on an inner surface of the second substrate, a plurality of partition walls located on the transparent anode, transmission holes formed among the partition walls, an organic layer located on the transparent anode and in the transmission holes, and a metal cathode located on the organic layer and the partition walls, wherein the metal cathode is electrically connected to a drain of the thin film transistor.

wherein the thin film transistor comprises a gate, a source metal layer and a drain metal layer, wherein a thickness of the source metal layer is smaller than a thickness of the drain metal layer; a passivation layer is further located on the source metal layer, the drain metal layer and the first substrate, and the passivation layer comprises a concave area and a convex area adjacent to the concave area, and a bottom of the concave area is aligned with a top surface of the drain metal layer and higher than a top surface of the source metal

layer to expose a part of the drain metal layer, and the metal anode on the organic layer correspondingly joints into the concave area and fits the bottom of the concave area, and the metal cathode is connected to the drain metal layer via the concave area; and

wherein the organic layer comprises a hole transporting layer contacting the transparent anode, an electron transport layer contacting the metal cathode and an emitting layer located between the hole transporting layer and the electron transport layer.

The benefits of the present invention are that the present invention provides an OLED display device and a manufacture method thereof. By forming the thin film transistors on the first substrate, and forming the organic layer and transparent anode on the second substrate, the transparent anode is located on the metal cathode and transparent, therefore, the selection of the cathode material is not influenced. Thus, the OLED display device is a top emitting type with high transmittance and a high aperture ratio. The manufacture method of an OLED display device provided by the present invention can manufacture an OLED display device with a high aperture ratio and high transmittance, and promote the yield and the productivity.

In order to better understand the characteristics and technical aspect of the invention, reference is made to the following detailed description of the present invention in combination with the drawings; however, the drawings are provided for reference and illustration only and are not intended to limiting of the invention.

BRIEF DESCRIPTION OF THE DRAWINGS

The technical solution and the beneficial effects of the present invention are best understood from the following detailed description with reference to the accompanying figures and embodiments.

In drawings,

FIG. 1 is a sectional diagram of a prior art bottom emitting AMOLED display device;

FIG. 2 is a sectional diagram of an OLED display device according to the present invention;

FIG. 3 is a flowchart of a manufacture method of an OLED display device according to the present invention; and

FIG. 4 is a sectional diagram of a thin film transistor and a passivation layer according to the present invention.

DETAILED DESCRIPTION OF PREFERRED EMBODIMENTS

For better explaining the technical solution and the effect of the present invention, the present invention will be further described in detail with the accompanying drawings and the specific embodiments.

Referring to FIGS. 2 and 4, the present invention provides an organic light emitting diode (OLED display device, which comprises a first substrate 100, a second substrate 200 spaced from and opposite to the first substrate 100, a plurality of thin film transistors 101 located on an inner surface of the first substrate 100, a transparent anode 201 located on an inner surface of the second substrate 200, a plurality of partition walls 202 formed on the transparent anode 201, transmission holes 203 formed among the partition walls 202, an organic layer 204 located on the transparent anode 201 and in the transmission holes 203, and a metal cathode 205 located on the organic layer 204 and the

partition walls **202**, wherein the metal cathode **205** is electrically connected to drains of the thin film transistors **101**.

The thin film transistor **101** comprises a gate **101a**, a source metal layer **101b** and a drain metal layer **101c**, wherein a thickness of the source metal layer **101b** is smaller than a thickness of the drain metal layer **101c**. A passivation layer **103** is further formed on the source metal layer **101b**, the drain metal layer **101c** and the first substrate **100**, and the passivation layer **103** comprises a concave area **101d** and a convex area **101e** adjacent to the concave area **101d**, wherein a bottom of the concave area **101d** is aligned with a top surface of the drain metal layer **101c** and higher than a top surface of the source metal layer **101b** to expose a part of the drain metal layer **101c**. The metal cathode **205** located on the organic layer **204** corresponds to and joints into the concave area **101d** and fits to the bottom of the concave area **101d**, such that the metal cathode **205** is connected to the drain metal layer **101c** via the concave area **101d**.

Specifically, a contact width of the partition wall **202** with the transparent anode **201** is smaller than a contact width thereof with the metal cathode **205**. A material of the transparent anode **201** is indium tin oxide. A material of the metal cathode **205** is one of calcium, aluminum and magnesium. The organic layer **204** comprises a hole transporting layer contacting the transparent anode **201**, an electron transport layer contacting the metal cathode **205** and an emitting layer located between the hole transporting layer and the electron transport layer. A voltage between the transparent anode **201** and the metal cathode **205** is controlled according to a control signal received by the thin film transistor **101** to make the organic layer **204** illuminate. The emitting light goes out by passing through the transparent anode **201** or goes out by passing through the transparent anode **201** after being reflected by the metal cathode **205**. Thus, the OLED display device of the present invention is a top emitting OLED display device with a specific high aperture ratio.

Referring to FIGS. **3** and **4**, the present invention further provides a manufacture method of an OLED display device, which comprises the following steps:

Step 1, forming a thin film transistor **101**, which comprises a gate **101a**, an active layer, a source **101b** and a drain **101c**, on the first substrate **100**.

A specific process of the step includes: forming a polysilicon layer on the first substrate **100**, wherein the polysilicon layer comprises an active layer and a source area and a drain area located on two ends of the active layer; covering an insulative layer on the poly-silicon layer, wherein the insulative layer covers the entirety of the active layer, a part of the source area and a part of the drain area; and forming the gate **101a** on the insulative layer of the active layer, and starting to coat metal layer on the exposed parts of the source area and the drain area to make the metal layer formed for forming the source metal layer **101b** and the drain metal layer **101c**, wherein a thickness of the source metal layer **101b** is smaller than a thickness of the drain metal layer **101c**.

Step 2, forming a passivation layer **103** on the source metal layer **101b**, the drain metal layer **101c** and the first substrate **100**, and applying a formation process to form a concave area **101d** on the passivation layer **103** and a convex area **101e** adjacent to the concave area **101d**,

wherein a bottom of the concave area **101d** is aligned with a top surface of the drain metal layer **101c** and higher than a top surface of the source metal layer **101b** to expose a part of the drain metal layer **101c**.

Step 3, forming a transparent anode **201** on a second substrate **200**.

In Step 3, a material of the transparent anode **201** is indium tin oxide.

Step 4, forming partition walls **202** on the transparent anode **201**, such that the partition walls **202** comprise a plurality of transmission holes **203** respectively corresponding to pixel areas.

The partition walls **202** is formed of a material comprising an organic material or an inorganic material and is formed such that a bottom contact width of the partition wall **202** with the transparent anode **201** is larger than a top contact width thereof with the metal cathode **205**.

Step 5, forming an organic layer **204** in the transmission holes **203** to be located on the transparent anode **201**.

In Step 5, the organic layer **204** comprises a hole transporting layer contacting the transparent anode **201**, an electron transport layer contacting the metal cathode **205** and an emitting layer located between the hole transporting layer and the electron transport layer. The organic layer **204** emits three colors of light including red, green and blue. A height of the organic layer **204** is lower than a height of the partition walls **202**.

Step 6, forming a metal cathode **205** on the organic layer **204** and the partition walls **202**.

In Step 6, a material of the metal cathode **205** is one of calcium, aluminum and magnesium.

Step 7, laminating the first substrate **100** and the second substrate **200**, such that the metal cathode **205** formed on the organic layer **204** corresponds to and joints into the concave area **101d** and fits to the bottom of the concave area **101d** and the metal cathode **205** is connected to the drain metal layer **101c** via the concave area **101d**.

In manufacturing these elements, the concave area **101d** of the passivation layer **103** is designed to correspond, in position, to the metal cathode **205** on the organic layer **204**, and an area of the concave area **101d** is larger than or equal to an area of the metal cathode **205** on the organic layer **204**, and the metal cathode **205** on the organic layer **204** can be completely jointed in the concave area **101d** of the passivation layer **103** when the first substrate and the second substrate are combined.

In the OLED display device and the manufacture method thereof provided by the present invention, by forming the thin film transistors on the first substrate, and forming the organic layer and transparent anode on the second substrate, the transparent anode is located on the metal cathode and transparent, therefore, the selection of the cathode material is not influenced. Thus, the OLED display device is a top emitting type with high transmittance and a high aperture ratio. The manufacture method of an OLED display device provided by the present invention can manufacture an OLED display device with a high aperture ratio and high transmittance, and promote the yield and the productivity.

The above provides only specific embodiments of the present invention, and the scope of the present invention is not limited to these embodiments. For those killed in the art, change or replacement, which is easily derived, should be covered by the protected scope of the invention. Thus, the protected scope of the invention should go by the subject claims.

What is claimed is:

1. A method for manufacturing an organic light emitting diode (OLED) display device that comprises a pixel area, comprising the following steps:

Step 1, forming a thin film transistor, which comprises a gate, a source metal layer, and a drain metal layer, on

7

a first substrate, wherein a thickness of the source metal layer is smaller than a thickness of the drain metal layer;

Step 2, forming a passivation layer on the source metal layer, the drain metal layer, and the first substrate such that the passivation layer comprises a surface on which a concave area and a convex area that adjacent to the concave area are formed,

wherein a bottom of the concave area is aligned with a top surface of the drain metal layer and higher than a top surface of the source metal layer to expose a part of the drain metal layer;

Step 3, forming a transparent anode on a second substrate;

Step 4, forming partition walls on the transparent anode, such that the partition walls define a transmission hole therebetween to correspond to the pixel area of the OLED display device;

Step 5, forming an organic layer in the transmission hole to be located on the transparent anode;

Step 6, forming a metal cathode on the organic layer and the partition walls; and

Step 7, laminating the first substrate and the second substrate together, such that the metal cathode formed on the organic layer corresponds to and joints into the

8

concave area and fits to the bottom of the concave area to have the metal cathode connected to the exposed part of the drain metal layer in the concave area.

2. The method as claimed in claim 1, wherein the concave area of the passivation layer corresponds, in position, to the metal cathode formed on the organic layer, and an area of the concave area is larger than or equal to an area of the metal cathode formed on the organic layer to allow the metal cathode to be completely received into and fit to the bottom of the concave area of the passivation layer to contact the exposed part of the drain metal layer.

3. The method as claimed in claim 1, wherein the transparent anode is formed of a material comprising indium tin oxide.

4. The method as claimed in claim 1, wherein the metal cathode is formed of a material comprising one of calcium, aluminum, and magnesium.

5. The method as claimed in claim 1, wherein the organic layer comprises a hole transporting layer that is in contact with the transparent anode, an electron transport layer that is in contact with the metal cathode, and an emitting layer located between the hole transporting layer and the electron transport layer.

* * * * *

专利名称(译)	OLED显示装置及其制造方法		
公开(公告)号	US9972668	公开(公告)日	2018-05-15
申请号	US15/821844	申请日	2017-11-24
[标]申请(专利权)人(译)	深圳市华星光电技术有限公司		
申请(专利权)人(译)	深圳市中国星光电科技有限公司.		
当前申请(专利权)人(译)	深圳市中国星光电科技有限公司.		
[标]发明人	SHI LONGQIANG WANG YIFAN		
发明人	SHI, LONGQIANG WANG, YIFAN		
IPC分类号	H01L27/32 H01L51/52 H01L51/00 H01L51/56		
CPC分类号	H01L27/3253 H01L27/3246 H01L27/3248 H01L51/0024 H01L51/5206 H01L51/56 H01L51/5221 H01L2251/558 H01L27/3262 H01L2227/323 H01L2251/301 H01L2251/308		
代理人(译)	程 , ANDREW C.		
优先权	201410742800.0 2014-12-08 CN		
其他公开文献	US20180108719A1		
外部链接	Espacenet USPTO		

摘要(译)

提供一种用于制造包括像素区域的OLED显示装置的方法。提供第一和第二基板。TFT布置在第一基板上。在TFT上形成钝化层，使得钝化层包括形成在其表面中的凹入区域，以暴露每个TFT的漏极的一部分。在第二基板上形成透明阳极。分隔壁布置在透明阳极上，以在它们之间限定分别对应于像素区域的透射孔。有机层形成在透明阳极上并位于透射孔中。在有机层和分隔壁上形成金属阴极，使得金属阴极可接收到凹入区域中并且可与每个TFT的漏极的暴露部分电接合。

